FORM PTO – 1449 *	ATTY DOCKET NO.:	ASC-025DV2C1
INFORMATION DISCLOSURE STATEMENT	APPLICANTS:	Cheng *et al.*
COPY	SERIAL NO.:	10/802,186
	FILING DATE:	March 17, 2004
	GROUP:	Not yet assigned

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	B2	0 514 018	11/19/1992	EP				No	Yes
	B3	0 587 520	03/16/1994	EP				No	Yes
	B4	0 683 522	11/22/1995	EP				No	Yes
	B5	0 828 296	03/11/1998	EP				No	Yes
	B6	0 829 908	03/18/1998	EP				No	Yes
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Examiner Name	Shouxiang Hu
Attorney Docket Number	ASC-025DV2C1

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	B51	JP-3-036717	02-18-1991			√
	B52	JP-6-244112	09-02-1994		Abstract only	√
	B53	JP-6-252046	09-09-1994		Abstract only	√
	B54	JP-61-141116	06-28-1986		Abstract only	√

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